

91 130 ... GaAs 26% 가

가 , (GaAs)

91 , 90 0.5% 가 , 90 16% 가 130

< > JAMS-CS

( :100 , %)

		GaAs	GaP	InP	
1986		4,314(110)	3,727( )	730( )	8,771(113)
		4,031( 92)	3,649( )	856( )	8,536(105)
		8,345(101)	7,376( )	1,586( )	17,307(109)
1987		4,192( 97)	4,594(123)	1,142(156)	9,928(113)
		4,205(104)	4,047(111)	1,018(119)	9,270(109)
		8,397(101)	8,641(117)	2,160(136)	19,198(111)
1988		4,255(102)	4,163( 91)	695( 61)	9,113( 92)
		4,194(100)	3,861( 95)	770( 76)	8,825( 95)
		8,449(101)	8,024( 93)	1,465( 68)	17,938( 93)
1989		4,550(107)	4,767(115)	1,042(150)	10,359(114)
		4,701(112)	4,436(115)	1,117(145)	10,254(116)
		9,251(109)	9,203(115)	2,159(147)	20,613(115)
1990		4,822(106)	5,350(112)	1,076(103)	11,248(109)
		6,124(130)	5,764(130)	1,075( 96)	12,963(126)
		10,946(118)	11,114(121)	2,151(100)	24,211(117)
1991		6,059(126)	5,981(112)	991( 92)	13,031(116)

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91 1% , LED( ) 가 IC 가, chip 89

130 3100 (結晶別) 가 90 26% 가 60 5900 , (GaP) 12% 가 59 8109 , (InP) 8% 9 9100

HEMT( ) 3.8% , 1.1%

< 1992/3/15>